

N-channel 100 V, 0.02 Ω typ., 24 A STripFET™ F7 Power MOSFET in a TO-220FP package

Datasheet - production data

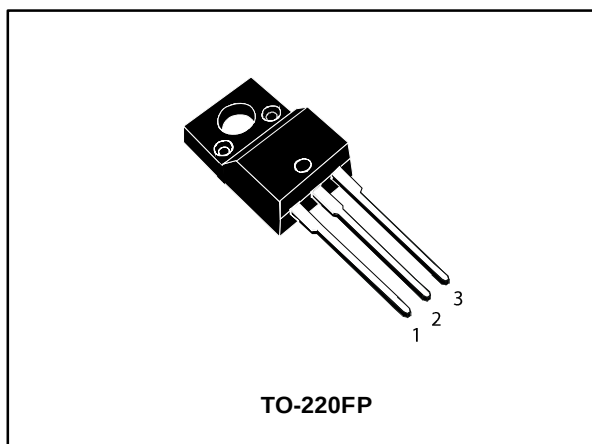
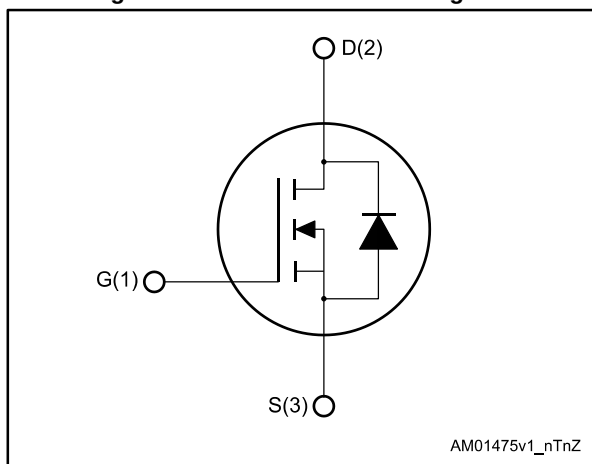


Figure 1: Internal schematic diagram



Features

- Among the lowest $R_{DS(on)}$ on the market
- Excellent FoM (figure of merit)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Table 1: Device summary

Order code	Marking	Package	Packing
STF30N10F7	30N10F7	TO-220FP	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate source voltage	20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ °C}$	24	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ °C}$	16	A
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	96	A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	25	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{ s}$; $T_C=25\text{ °C}$)	2500	V
T_J	Operating junction temperature range	-55 to 175	°C
T_{stg}	Storage temperature range		

Notes:⁽¹⁾Current is limited by package.⁽²⁾Pulse width limited by safe operating area.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	6	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	°C/W

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0 V, I _D = 250 μA	100			V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0 V, V _{DS} = 100 V			1	μA
		V _{GS} = 0 V, V _{DS} = 100 V, T _C = 125 °C ⁽¹⁾			100	μA
I _{GSS}	Gate-body leakage current	V _{DS} = 0 V, V _{GS} = +20 V			100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.5		4.5	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 16 A		0.02	0.024	Ω

Notes:

⁽¹⁾Defined by design, not subject to production test

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 50 V, f = 1 MHz, V _{GS} = 0 V	-	1270	-	pF
C _{oss}	Output capacitance		-	290	-	pF
C _{rss}	Reverse transfer capacitance		-	24	-	pF
Q _g	Total gate charge	V _{DD} = 50 V, I _D = 32 A, V _{GS} = 10 V (see Figure 14: "Test circuit for gate charge behavior")	-	19	-	nC
Q _{gs}	Gate-source charge		-	9	-	nC
Q _{gd}	Gate-drain charge		-	4.5	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 50 V, I _D = 16 A, R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 13: "Test circuit for resistive load switching times")	-	12	-	ns
t _r	Rise time		-	17.5	-	ns
t _{d(off)}	Turn-off delay time		-	22	-	ns
t _f	Fall time		-	5.6	-	ns

Table 7: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 24\text{ A}$, $V_{GS} = 0$	-		1.1	V
I_{rr}	Reverse recovery time	$I_{SD} = 24\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 80\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$, (see Figure 15: "Test circuit for inductive load switching and diode recovery times")	-	41		ns
Q_{rr}	Reverse recovery charge		-	47		nC
I_{RRM}	Reverse recovery current		-	2.3		A

Notes:

⁽¹⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

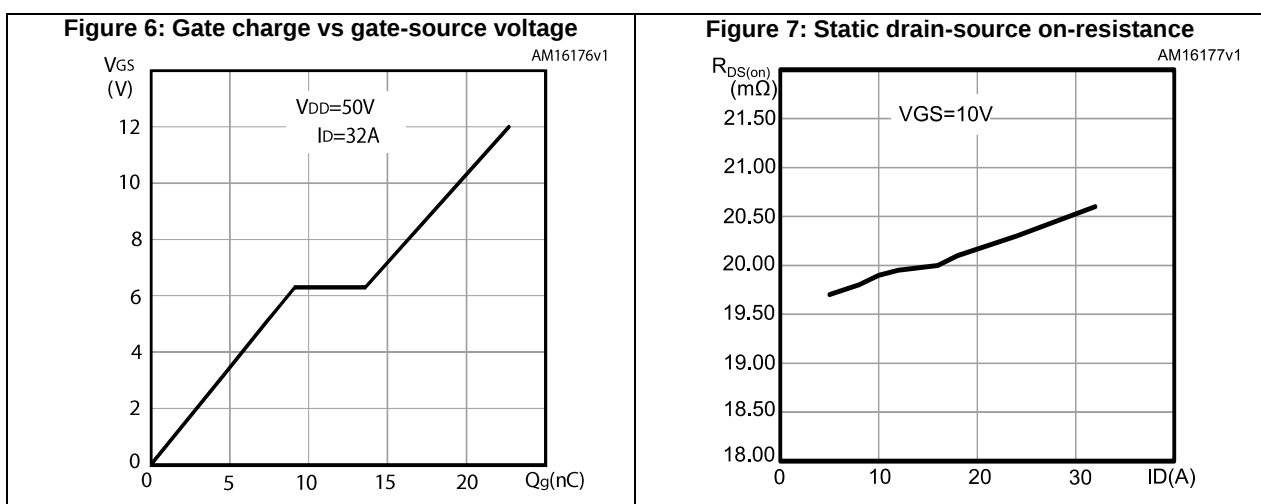
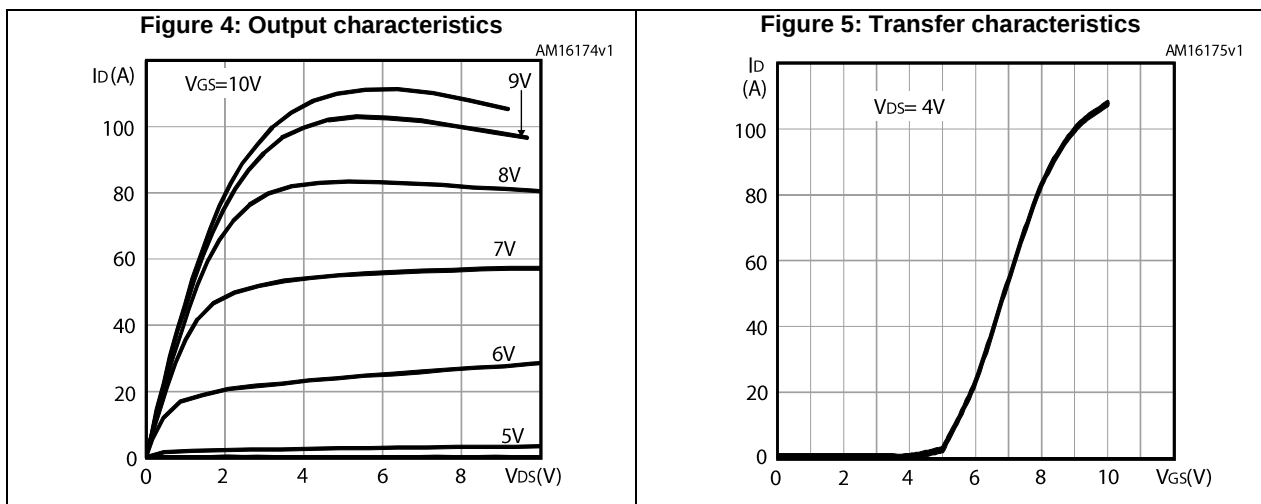
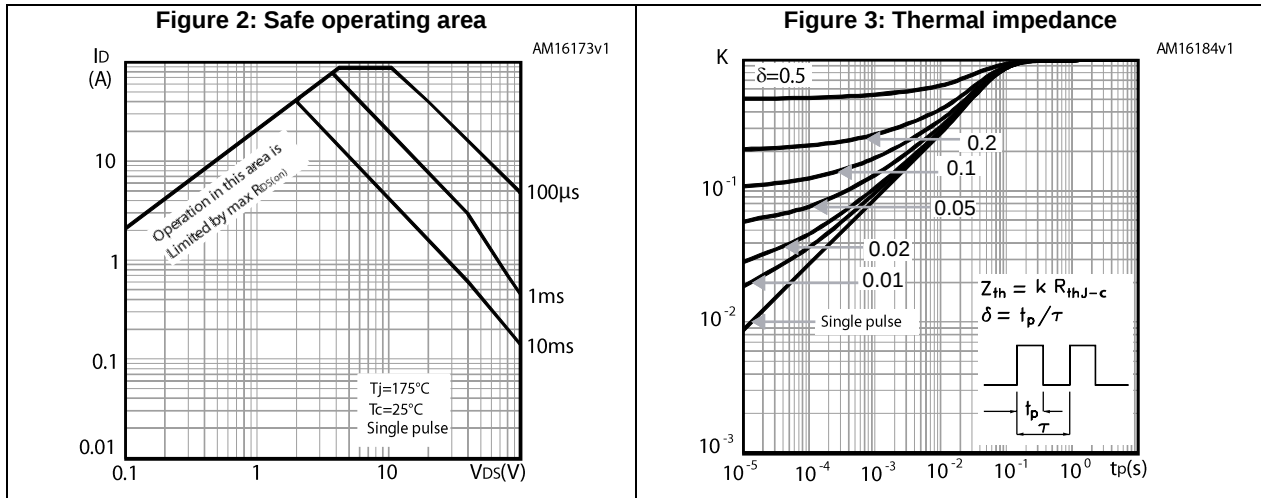


Figure 8: Capacitance variations

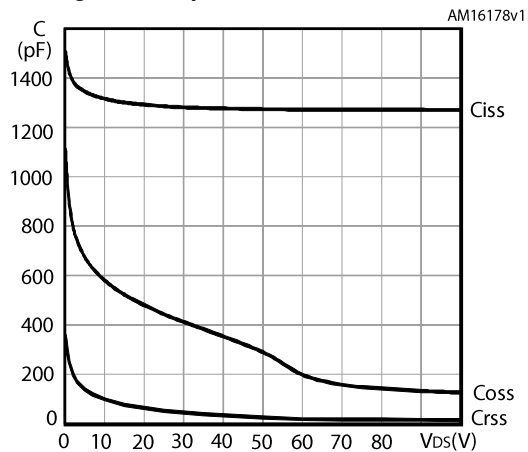


Figure 9: Normalized gate threshold voltage vs temperature

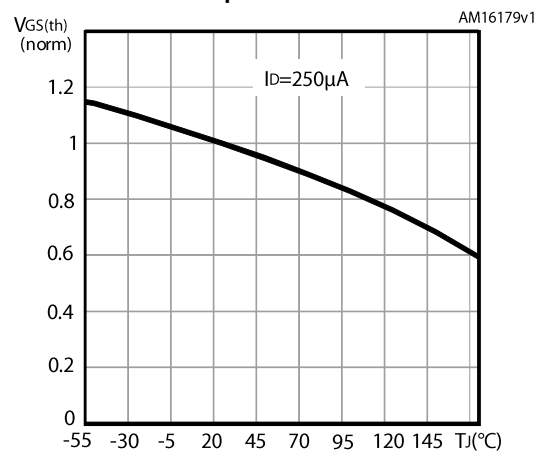


Figure 10: Normalized on-resistance vs temperature

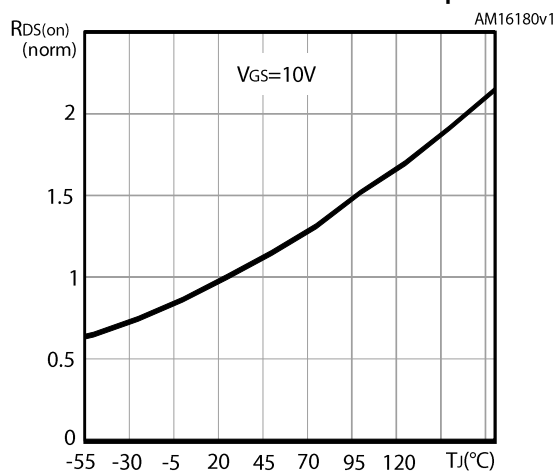


Figure 11: Normalized V(BR)DSS vs temperature

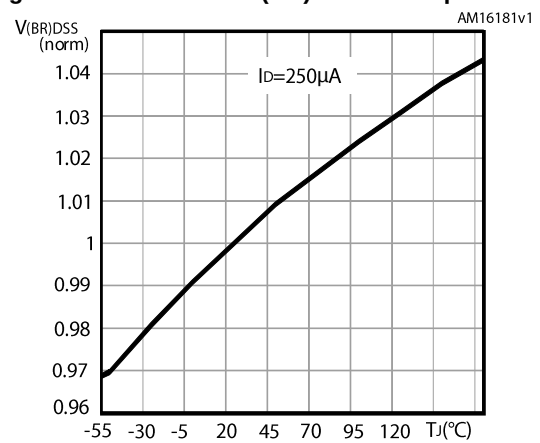
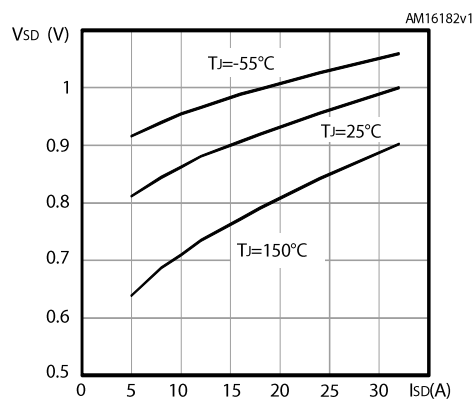
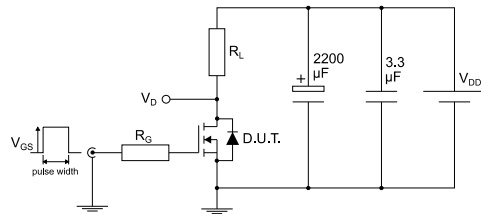


Figure 12: Source-drain diode forward characteristics



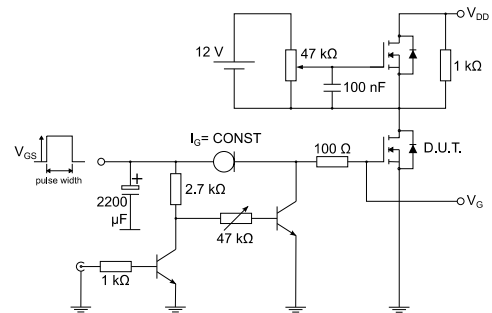
3 Test circuits

Figure 13: Test circuit for resistive load switching times



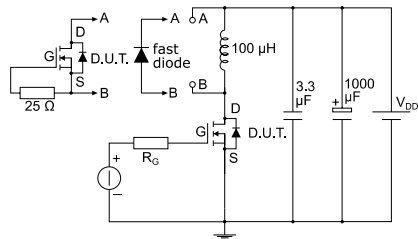
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Figure 14: Test circuit for gate charge behavior



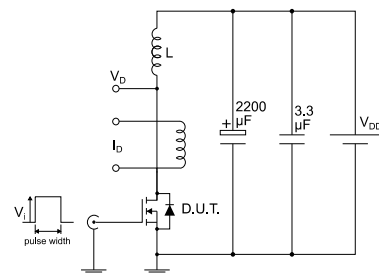
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Figure 15: Test circuit for inductive load switching and diode recovery times



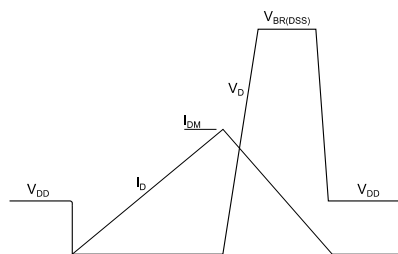
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Figure 16: Unclamped inductive load test circuit



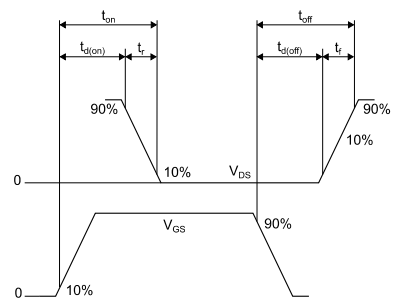
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Figure 17: Unclamped inductive waveform



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Figure 18: Switching time waveform



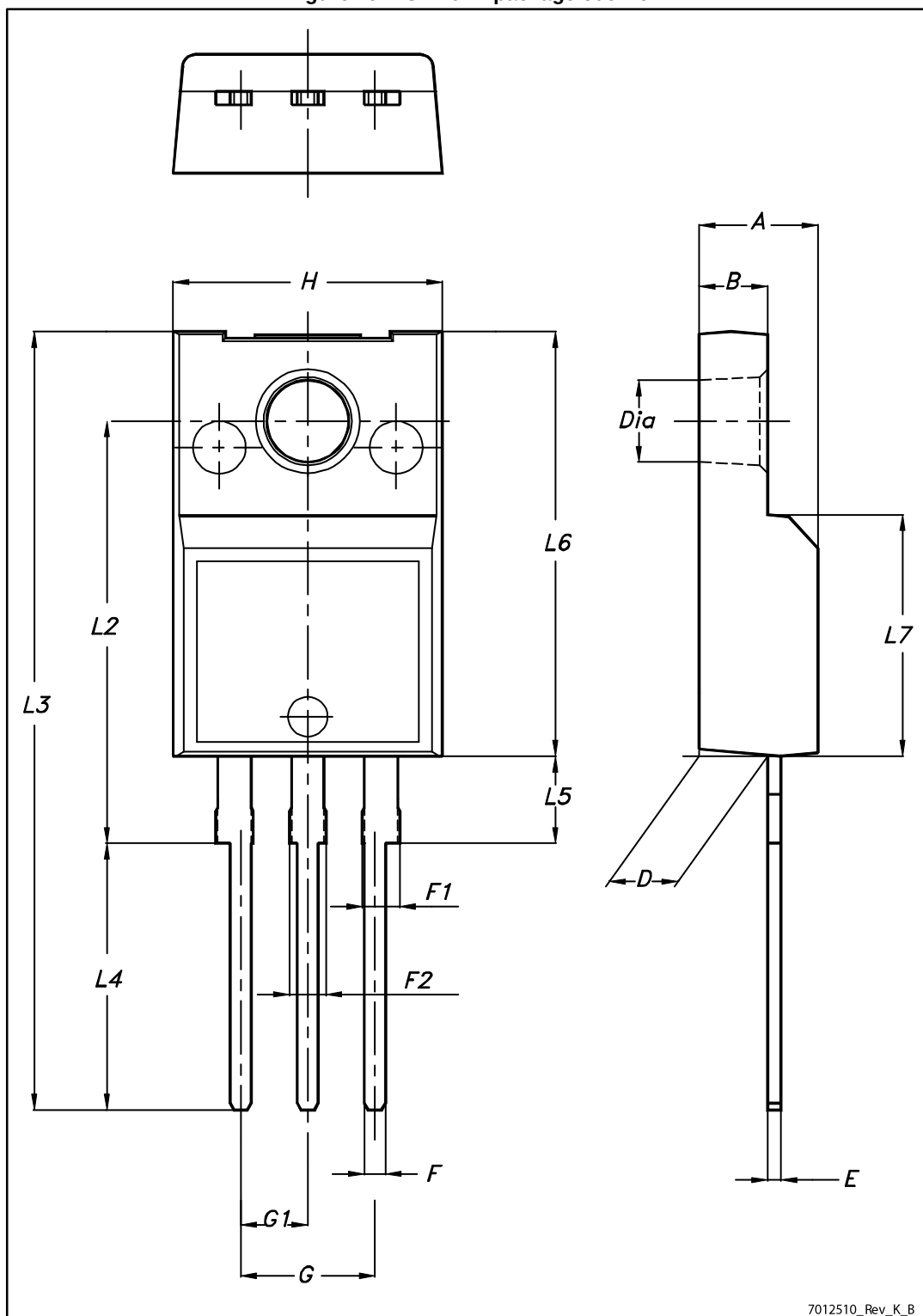
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

4.1 TO-220FP type A package information

Figure 19: TO-220FP package outline



7012510_Rev_K_B

Table 8: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

5 Revision history

Table 9: Document revision history

Date	Revision	Changes
15-Sep-2016	1	First release.

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